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CSD19536KCS, 100 V N-Channel NexFET™ Power MOSFET

Check for Samples: CSD19536KCS

FEATURES

- Ultra-Low Q_q and Q_{qd}
- Low Thermal Resistance
- · Avalanche Rated
- Pb-Free Terminal Plating
- RoHS Compliant
- Halogen Free
- TO-220 Plastic Package

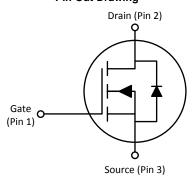
APPLICATIONS

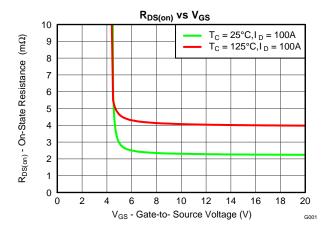
- Secondary Side Synchronous Rectifier
- Motor Control

DESCRIPTION

This 100 V, 2.3 m Ω , TO-220 NexFETTM power MOSFET is designed to minimize losses in power conversion applications.

Pin Out Drawing





PRODUCT SUMMARY

T _A = 25°	С	TYPICAL VA	UNIT		
V_{DS}	Drain-to-Source Voltage	100	V		
Q_g	Gate Charge Total (10 V)	118	nC		
Q_{gd}	Gate Charge Gate to Drain	Charge Gate to Drain 17			
D	Drain-to-Source On Resistance	V _{GS} = 6 V 2.		mΩ	
R _{DS(on)}	Diam-to-Source On Resistance	V _{GS} = 10 V 2.3		mΩ	
V _{GS(th)}	Threshold Voltage	2.5		V	

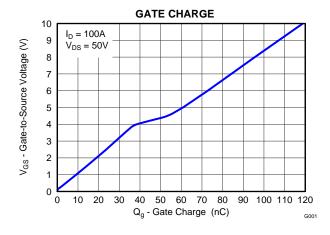
ORDERING INFORMATION

Device	Package	Media	Qty	Ship
CSD19536KCS	TO-220 Plastic Package	Tube	50	Tube

ABSOLUTE MAXIMUM RATINGS

T _A = 2	5°C	VALUE	UNIT	
V_{DS}	Drain-to-Source Voltage	100	V	
V_{GS}	Gate-to-Source Voltage	±20	V	
	Continuous Drain Current (Package limited)	150		
I _D	Continuous Drain Current (Silicon limited), $T_C = 25^{\circ}C$	259	Α	
	Continuous Drain Current (Silicon limited), $T_C = 100$ °C	183		
I_{DM}	Pulsed Drain Current (1)	224	Α	
P_D	Power Dissipation	375	W	
T_J , T_{STG}	Operating Junction and Storage Temperature Range	-55 to 175	°C	
E _{AS}	Avalanche Energy, single pulse I_D = 127 A, L = 0.1 mH, R_G = 25 Ω	806	mJ	

(1) Pulse duration ≤ 300 µs, Duty cycle ≤ 1%



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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

ELECTRICAL CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

$\begin{array}{c} V_{GS(th)} & \text{Gate-to-Source Threshold Voltage} \\ V_{DS} = V_{GS}, \ I_D = 250 \ \mu\text{A} \\ \hline \\ R_{DS(on)} & \text{Drain-to-Source On Resistance} \\ \hline \\ Q_{GS} = 6 \ V, \ I_D = 100 \ A \\ \hline \\ V_{GS} = 10 \ V, \ I_D = 100 \ A \\ \hline \\ Q_{SS} = 10 \ V, \ I_D$		PARAMETER	TEST CONDITIONS	MIN TYP	MAX	UNIT
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Static Ch	naracteristics				
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	3V _{DSS}	Drain-to-Source Voltage	V _{GS} = 0 V, I _D = 250 μA	100		V
$\begin{array}{c} V_{GS(th)} & \text{Gate-to-Source Threshold Voltage} \\ V_{DS} = V_{GS}, \ I_D = 250 \ \mu\text{A} \\ V_{GS} = 6 \ V, \ I_D = 100 \ A \\ V_{GS} = 10 \ V, \ I_D = 100 \ A \\ V_{GS} = 10 \ V, \ I_D = 100 \ A \\ V_{GS} = 10 \ V, \ I_D = 100 \ A \\ V_{GS} = 10 \ V, \ I_D = 100 \ A \\ V_{GS} = 10 \ V, \ I_D = 100 \ A \\ V_{GS} = 10 \ V, \ I_D = 100 \ A \\ V_{GS} = 10 \ V, \ I_D = 100 \ A \\ V_{GS} = 10 \ V, \ I_D = 100 \ A \\ V_{GS} = 10 \ V, \ I_D = 100 \ A \\ V_{GS} = 10 \ V, \ I_D = 100 \ A \\ V_{GS} = 10 \ V, \ I_D = 100 \ A \\ V_{GS} = 10 \ V, \ I_D = 100 \ A \\ V_{GS} = 10 \ V, \ I_D = 100 \ A \\ V_{GS} = 10 \ V, \ I_D = 100 \ A \\ V_{GS} = 10 \ V, \ I_D = 100 \ A \\ V_{GS} = 10 \ V, \ I_D = 100 \ A \\ V_{GS} = 10 \ V, \ I_D = 100 \ A \\ V_{GS} = 10 \ V, \ I_D = 100 \ A \\ V_{GS} = 10 \ V, \ I_D = 100 \ A \\ V_{DS} = 10 \ V, \ I_D = $	DSS	Drain-to-Source Leakage Current	V _{GS} = 0 V, V _{DS} = 80 V		1	μΑ
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	GSS	Gate-to-Source Leakage Current	V _{DS} = 0 V, V _{GS} = 20 V		100	nA
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	V _{GS(th)}	Gate-to-Source Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2.1 2.5	3.2	V
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$		Proin to Course On Registeres	V _{GS} = 6 V, I _D = 100 A	2.5	3.2	mΩ
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	™DS(on)	Drain-to-Source On Resistance	$V_{GS} = 10 \text{ V}, I_D = 100 \text{ A}$	2.3	2.7	mΩ
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	9 _{fs}	Transconductance	V _{DS} = 10 V, I _D = 100 A	307		S
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	Dynamic	: Characteristics				
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	C _{iss}	Input Capacitance		9250	12000	pF
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	Coss	Output Capacitance	$V_{GS} = 0 \text{ V}, V_{DS} = 50 \text{ V}, f = 1 \text{ MHz}$	1820	2370	pF
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	Crss	Reverse Transfer Capacitance		47	61	pF
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	R _G	Series Gate Resistance		1.4	2.8	Ω
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	Q_g	Gate Charge Total (10 V)		118	153	nC
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	Q_{gd}	Gate Charge Gate to Drain	V - 50 V I - 100 A	17		nC
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	Q_{gs}	Gate Charge Gate to Source	V _{DS} = 50 V, I _D = 100 A	37		nC
$\begin{array}{c ccccc} t_{d(on)} & \text{Turn On Delay Time} & & & & & & & \\ t_r & \text{Rise Time} & & & & & & & \\ t_{d(off)} & \text{Turn Off Delay Time} & & & & & & \\ t_f & \text{Fall Time} & & & & & & & \\ \end{array}$	Q _{g(th)}	Gate Charge at V _{th}		24		nC
$\begin{array}{c c} t_{d(on)} & \text{Turn On Delay Time} \\ \hline t_r & \text{Rise Time} \\ \hline t_{d(off)} & \text{Turn Off Delay Time} \\ \hline t_f & \text{Fall Time} \\ \end{array} \begin{array}{c c} V_{DS} = 50 \text{ V}, V_{GS} = 10 \text{ V}, \\ I_{DS} = 100 \text{ A}, R_G = 0 \Omega \\ \hline \end{array} \begin{array}{c c} 38 \\ \hline 5 \\ \hline \end{array}$	Q _{oss}	Output Charge	V _{DS} = 50 V, V _{GS} = 0 V	335		nC
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	d(on)	Turn On Delay Time		14		ns
$ \begin{array}{c c} t_{d(off)} & \text{Turn Off Delay Time} & I_{DS} = 100 \text{ A}, R_G = 0 \ \Omega \\ \hline t_f & \text{Fall Time} & 5 \end{array} $	r	Rise Time	$V_{DS} = 50 \text{ V}, V_{GS} = 10 \text{ V},$	8		ns
	d(off)	Turn Off Delay Time		38		ns
Diode Characteristics	if	Fall Time		5		ns
	Diode Ch	naracteristics				
V_{SD} Diode Forward Voltage $I_{SD} = 100 \text{ A}, V_{GS} = 0 \text{ V}$ 0.9	V _{SD}	Diode Forward Voltage	I _{SD} = 100 A, V _{GS} = 0 V	0.9	1.1	V
Q_{rr} Reverse Recovery Charge $V_{DS} = 50 \text{ V, I}_F = 100 \text{ A},$ 548	Q _{rr}	Reverse Recovery Charge	V _{DS} = 50 V, I _F = 100 A,	548		nC
t_{rr} Reverse Recovery Time $di/dt = 300 \text{ A/}\mu\text{s}$ 110	rr	Reverse Recovery Time		110		ns

THERMAL CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

	PARAMETER	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Thermal Resistance Junction to Case			0.4	°C/W
$R_{\theta JA}$	Thermal Resistance Junction to Ambient			62	°C/W

Product Folder Links: CSD19536KCS

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TYPICAL MOSFET CHARACTERISTICS

(T_A = 25°C unless otherwise stated)

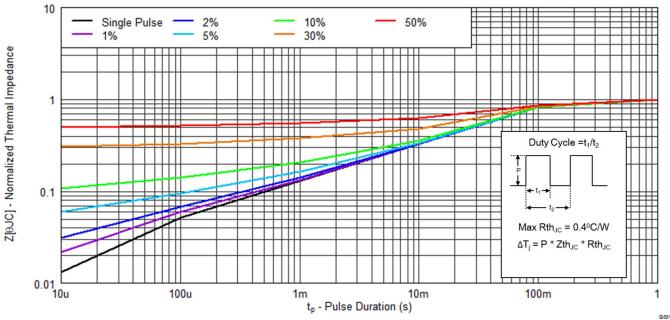
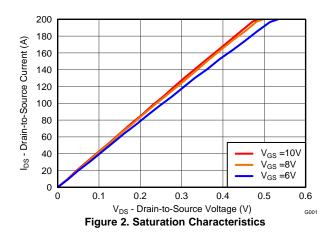
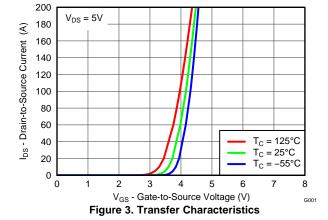


Figure 1. Transient Thermal Impedance





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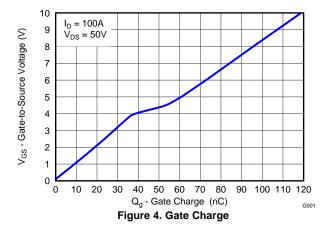
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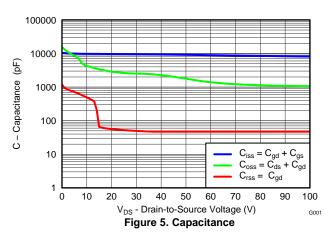
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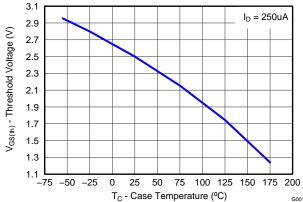
TEXAS INSTRUMENTS

TYPICAL MOSFET CHARACTERISTICS (continued)

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$







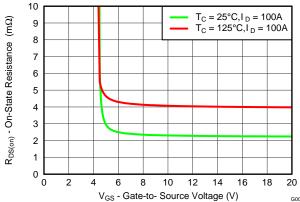
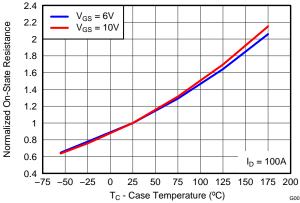


Figure 6. Threshold Voltage vs Temperature

Figure 7. On-State Resistance vs Gate-to-Source Voltage



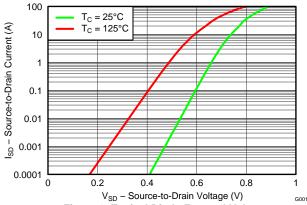


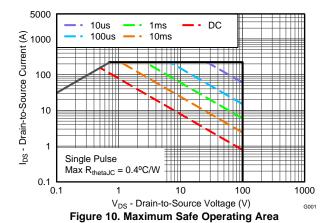
Figure 8. Normalized On-State Resistance vs Temperature

Figure 9. Typical Diode Forward Voltage

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TYPICAL MOSFET CHARACTERISTICS (continued)

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$



1000 T_C = 25°C T_C = 125°C T

Figure 11. Single Pulse Unclamped Inductive Switching

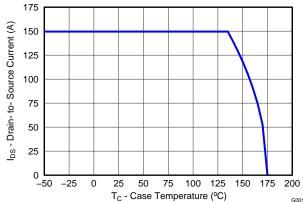


Figure 12. Maximum Drain Current vs Temperature

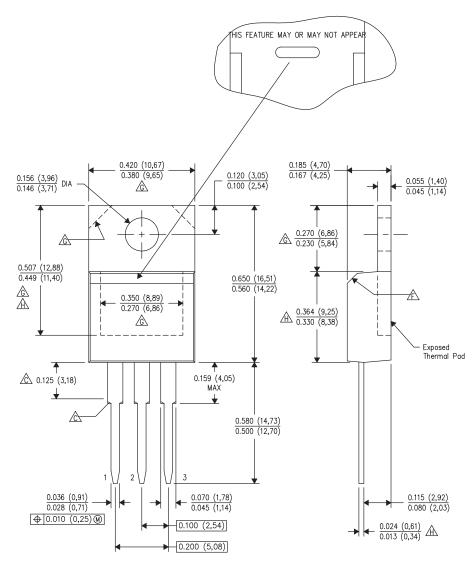
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Instruments

MECHANICAL DATA

KCS Package Dimensions



NOTES:

- A. All linear dimensions are in inches (millimeters).

 B. This drawing is subject to change without notice.
- This drawing is subject to change without notice.
- Lead dimensions are not controlled within this area. Chamfer may or may not appear
 D. All lead dimensions apply before solder dip.
 E. The center lead is in electrical contact with the mounting tab.

- The chamfer is optional.
- Thermal pad contour optional within these dimensions.
- A Falls within JEDEC TO-220 variation AB, except minimum lead thickness, minimum exposed pad length, and maximum body length.

Table 1. Pin Configuration

Position	Designation
Pin 1	Gate
Pin 2 / Tab	Drain
Pin 3	Source

Submit Documentation Feedback



PACKAGE OPTION ADDENDUM

5-Feb-2014

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
CSD19536KCS	ACTIVE	TO-220	KCS	3	50	Pb-Free (RoHS)	CU SN	N / A for Pkg Type	-55 to 175		Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes. **Pb-Free** (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead/Ball Finish Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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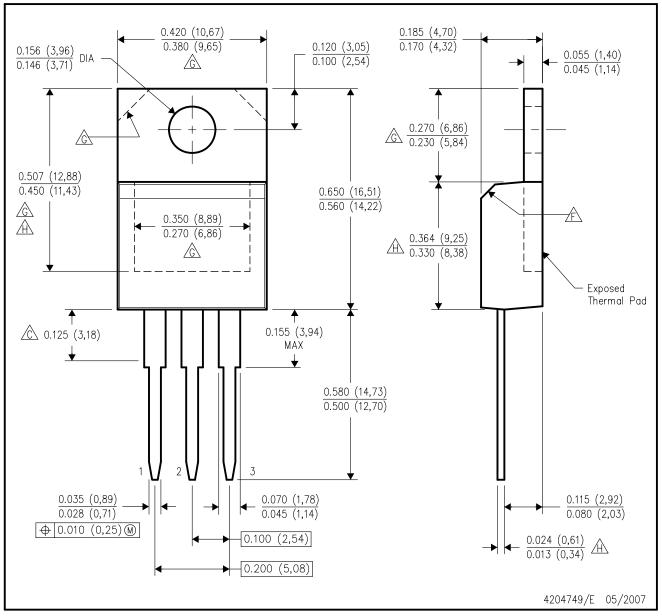




5-Feb-2014

KCS (R-PSFM-T3)

PLASTIC FLANGE-MOUNT PACKAGE



NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Lead dimensions are not controlled within this area.
- D. All lead dimensions apply before solder dip.
- E. The center lead is in electrical contact with the mounting tab.
- The chamfer is optional.
- Thermal pad contour optional within these dimensions.
- Falls within JEDEC TO-220 variation AB, except minimum lead thickness, minimum exposed pad length, and maximum body length.



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